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TABLE OF CONTENTS

Tuesday, March 25

SESSION 1: Matching I – Characterisation

1.1 – Operational Amplifier Based Test Structure For Transistor Threshold Voltage Variation 3
Brian L. Ji, Dale J. Pearson, Isaac Lauer, Franco Stellari, David J. Frank, Leland Chang, and Mark B. Ketchen
IBM T.J. Watson Research Center, NY, USA

1.2 – A Study of Variation in Characteristics and Subthreshold Humps for 65-nm SRAM Using Newly Developed SRAM Cell Array Test Structure 8
A. Mizumura[1], T. Suzuki[1], T. Arima[2], H. Maeda[2], and H. Ammo[1]
[1]*Semiconductor Technology Development Division, Sony Corp.* [2]*Sony LSI Design Incorporated, Kanagawa, Japan*

1.3 – Mismatch Characterization of a High Precision Resistor Array Test Structure 11
Weidong Tian, Philipp Steinmann, Eric Beach, Imran Khan and Praful Madhani
Texas Instruments Inc. USA

1.4 – Rapid Characterization of Parametric Distributions Using a Multi-meter . . 17
Jerry Hayes, Kanak Agarwal, Sani Nassif
IBM Austin Research Labs, TX, USA

SESSION 2: Resistivity

2.1 – Beyond van der Pauw: Sheet Resistance Determination of Arbitrarily Shaped Planar Four-Terminal Devices with Extended Contacts 23
Martin Cornils and Oliver Paul
Department of Microsystems Engineering (IMTEK), University of Freiburg, Germany

2.2 – Investigation of Electrical and Optical CD Measurement Techniques for the Characterisation of On-Mask GHOST Proximity Corrected Features 29
A. Tsiamis[1], S. Smith[1], M. McCallum[2], A.C. Hourd[3], O. Toublan[4], J.T.M. Stevenson[1] and A.J. Walton[1]
[1]*The University of Edinburgh,* [2]*Nikon Precision Europe GmbH,* [3]*Compugraphics International Ltd., UK* [4]*Mentor Graphics Ltd., France*

2.3 – **Comparison of Measurement Techniques for Advanced Photomask Metrology** **35**
S. Smith[1], A. Tsiamis[1], M. McCallum[2], A.C. Hourd[3], J.T.M. Stevenson[1], A.J. Walton[1], R.G. Dixson[4], R.A. Allen[4], J.E. Potzick[4], M.W. Cresswell[4] and N.G. Orji[4]
[1]*The University of Edinburgh,* [2]*Nikon Precision Europe GmbH,* [3]*Compugraphics International Ltd.,* [4]*National Institute of Standards and Technology*

SESSION 3: Yield and Reliability I

3.1 – **Electromigration : from package to wafer level thanks to a heating coil structure** **43**
C. Chappaz, P. Waltz, L. Castellon
STMicroelectronics, Crolles CEDEX, France

3.2 – **Life condition monitoring on smart power devices using a sequence of current and charge-based capacitance measurements** **46**
Zhenqiu Ning[1], Erwin de Vylder[1], Filip Bauwens[1], Basil Vlachakis[1], H-X Delecourt[1], Renaud Gillon[1], Patrick Van Torre[2] and Dan Hegsted[1]
[1]*AMI Semiconductor Belgium bvba, Belgium,* [2]*Hogeschool Gent, Belgium*

3.3 – **Mixed Test Structure for Process Variation and Hard Defect Detection** **52**
F. Rigaud[1,2], J.M. Portal[1], H. Aziza[1], D. Née[2], J. Vast[2], F. Argoud[2], B. Borot[3]
[1]*L2MP - Laboratoire Matériaux et Microélectronique de Provence,* [2]*STMicroelectronics, Rousset,* [3]*STMicroelectronics, Crolles, France*

3.4 – **Short-flow Test Chip Utilizing Fast Testing for Defect Density Monitoring in 45nm** **56**
Muthu Karthikeyan[1], William Cote[1], Louis Medina[1], Ernesto Shiling[1], Arthur Gasasira[1], Amy Henning[1], William Ferrante[1], Mark Craig[2], and Thomas Merbeth[3]
[1]*IBM Systems and Technology Group, NY, USA,* [2]*AMD Austin, TX, USA,* [3]*AMD Saxony, Dresden, Germany*

SESSION 4: Poster Presentations

4.1 – **Conduit Diffusion of Dopants in Tungsten Silicide Layers** **65**
S. Liao, M. Bain, P. Baine, D.W. McNeill, B.M. Armstrong and H.S. Gamble
Queen's University of Belfast, UK

4.2 – A Novel High Speed Automatic Layout System to Place and Route Test Structures for Parametric Test Capability 71

Andrew J. West[1], Samrat Mondal[2], Devjyoti Patra[2], Kalyan Goswami[2] and Shamik Sural[2]

[1]*National Semiconductor Corp, Santa Clara, CA, USA,* [2]*Indian Institute of Technology, Kharagpur, India*

4.3 – A Test Structure for Channel Length Engineering of NAND Gates in Standard Cell Library 76

T. Matsuda[1], Y. Sugiyama[1], J. Takakuwa[1], H. Iwata[1], T. Ohzone[2]

[1]*Department of Information Systems Engineering, Toyama Prefectural University,* [2]*Dawn Enterprise, Japan*

4.4 – Test Structure for Characterising Low Voltage Coplanar EWOD System . . . 80

Yifan Li[1], Yoshio Mita[1,2], Les Haworth[1], William Parkes[1], Masanori Kubota[2], Anthony Walton[1]

[1]*University of Edinburgh, UK,* [2]*University of Tokyo, Japan*

4.5 – Measurement of the MOSFET Drain Current Variation Under High Gate Voltage 86

Tetsuo Chagawa[1], Kazuo Terada[1], Jianyu Xiang[1], Katsuhiro Tsuji[1], Takaaki Tsunomura[2] and Akio Nishida[2]

[1]*Faculty of Information Sciences, Hiroshima City University, Japan,* [2]*MIRAI-Selete, Tsukuba, Japan*

4.6 – Spacing Impact on MOSFET Mismatch 90

A. Cathignol[1,3] , S. Mennillo[2], S. Bordez[1], L. Vendrame[2], G. Ghibaudo[3]

[1]*STMicroelectronics, Crolles, France,* [2]*STMicroelectronics, Advanced R&D, Italy,* [3]*IMEP, Minatec, Grenoble, France*

4.7 – Highly Automated Test Chip Layout and Test Plan Development for Parametric Electrical Test 96

Ann Gabrys, Wendy Greig, Andrew J. West, Philipp Lindorfer, and William French

National Semiconductor Corp., Santa Clara, CA, USA

4.8 – Circular Geometry MOS Transistor Analysis of SOI Substrates for High Energy Physics Particle Detectors 101

S.L. Suder[1], F.H. Ruddell[1], J.H. Montgomery[1], B.M. Armstrong[1], H.S. Gamble[1], G. Casse[2], T. Bowcock[2], P.P. Allport[2]

[1]*Northern Ireland Semiconductor Research Centre, Queen's University Belfast, UK,* [2]*Liverpool Detector Centre, University of Liverpool, UK*

SESSION 5: 3D Integration

5.1 – Prediction of Stress-Induced Characteristics Changes for Small-scale Analog IC 107

Naohiro Ueda, Eri Nishiyama, Hideyuki Aota, Hirobumi Watanabe

Electronic Devices Company, Ricoh Co. Ltd., Japan

5.2 – Test Structures for the Measurement and Optimisation of Bond Strength for Anodic Bonding of Glass to Dielectric Thin Films 111

G. Cummins, H. Lin and A.J. Walton

The University of Edinburgh, UK

5.3 – Test Structures For The Evaluation Of 3D Chip Interconnection Schemes 117

A. Mathewson[1,2], J. Brun[2], R. Franiatte[2], A. Nowodzinski[2], R. Ancient[2], N. Sillon[2], F. Depoutot[3] and B. Dubois-Bonvalot[3]

[1]*Tyndall National Institute, Cork, Ireland,* [2]*CEA-Leti-Minatec, Grenoble,* [3]*Hardware Research Group, Gemalto, Grenoble, France*

5.4 – An Evaluation of Test Structures for Measuring the Contact Resistance of 3-D Bonded Interconnects 123

H. Lin, S. Smith, J.T.M. Stevenson, A.M. Gundlach, C.C. Dunare, and A.J. Walton

The University of Edinburgh, UK

SESSION 6: Yield and Reliability II

6.1 – High Density Test Structure Array for Accurate Detection and Localization of Soft Fails 131

Christopher Hess[1], Michele Squcciarini[1], Shia Yu[1], Jonathan Burrows[1], Jianjun Cheng[2], Ron Lindley[2], Andrew Swimmer[2], Steven Winters[2]

[1]*PDF Solutions Inc., San Jose, USA,* [2]*PDF Solutions Inc., San Diego, USA*

6.2 – New method for non destructive snap-back characterization in multifinger power MOSFETs 137

François Dieudonné[1], Aurore Constant[2], Julien Rosa[1], Benoit Gautheron[1], Jean-François Revel[1]

[1]*STMicroelectronics, Crolles, France,* [2]*SID/CNM, Bellaterra, Spain*

6.3 – Test Circuit for Measuring Pulse Widths of Single-Event Transients Causing Soft Errors **142**
Balaji Narasimham, Matthew J. Gadlage, Bharat L. Bhuva, Ronald D. Schrimpf, Lloyd W. Massengill, W. Timothy Holman, Arthur F. Witulski, Kenneth F. Galloway
Vanderbilt University, Nashville, TN 37235, USA

6.4 – CMOS Latch Metastability Characterization at the 65-nm-Technology Node **147**
Manjul Bhushan[1], Mark B. Ketchen[2] and Koushik K. Das[2]
190 [1]*IBM Systems and Technology Group, NY, USA,* [2]*IBM Research, T.J. Watson Research Center, NY, USA*

SESSION 7: MOS Modeling and Characterisation

7.1 – Characterization of MOSFETs Intrinsic Performance using the In-Wafer Advanced Kelvin-Contact Device Structure for High Performance CMOS LSIs **155**
R. Kuroda[1], A. Teramoto[2], T. Komuro[3], W. Cheng[2], S. Watabe[1], C.F. Tye[1], S. Sugawa[1] and T. Ohmi[2]
[1]*Graduate School of Engineering, Tohoku University,* [2]*New Industry Creation Hatchery Center, Tohoku University,* [3]*Agilent Technologies International Japan Ltd.*

7.2 – New Y-function-based methodology for accurate extraction of electrical parameters on nano-scaled MOSFETs **160**
Dominique Fleury[1,2], Antoine Cros[1], Hugues Brut[1], Gérard Ghibaudo[2]
[1]*STMicroelectronics, Crolles,* [2]*IMEP, Grenoble, France*

7.3 – A Novel Biasing Technique for Addressable Parametric Arrays **166**
Brad Smith[1], Uma Annamalai[2], Alexandre Arriordaz[1], Venkat Kolagunta[1], Jeff Schmidt[1] and Mehul Shroff[1]
[1]*Freescale Semiconductor, Austin, TX,* [2]*University of Arkansas, AR, USA*

SESSION 8: RF

8.1 – 2.6GHz RF Inductive Power Delivery for Contactless On-Wafer Characterization **175**
Jonathan Tompson, Adam Dolin, and Peter Kinget
Department of Electrical Engineering, Columbia University, NY, USA

8.2 – Advanced Test Structure Design for Dielectric Characterisation of Novel High-K Materials 180
John A. O'Sullivan[1], Wenbin Chen[2], Kevin G. McCarthy[1] and Gabriel M. Crean[1]
[1]*Department of Electrical and Electronic Engineering, University College Cork, Ireland,* [2]*Tyndall National Institute, Ireland*

8.3 – Characterization of T-Shape Terminal Impedances of Differential Short Stubs in Advanced CMOS Technology 185
Chiaki Inui and Minoru Fujishima
University of Tokyo, Japan

8.4 – Identifying dielectric and resistive electrode losses in high-density capacitors at radio frequencies 190
M.P.J. Tiggelman[1], K. Reimann[2], J. Liu[2], M. Klee[3], W. Keur[3], R. Mauczock[3], J. Schmitz[1] and R.J.E. Hueting[1]
[1]*MESA+ Research Institute for Nanotechnology, University of Twente,* [2]*NXP Semiconductors,* [3]*Philips Research, The Netherlands*

SESSION 9: Interconnect

9.1 – A Study of Cross-Bridge Kelvin Resistor Structures for Reliable Measurement of Low Contact Resistances 199
N. Stavitski[1], J.H. Klootwijk[2], H.W. van Zeijl[3], A.Y. Kovalgin[1] and R.A.M. Wolters[1,4]
[1]*MESA+ Institute for Nanotechnology, University of Twente,* [2]*Philips Research,* [3]*DIMES, Delft University of Technology,* [4]*NXP Research Eindhoven, The Netherlands*

9.2 – Comb Capacitor Structures for Measurement of a Post-processed Layer ... 205
D. Roy[1], J.H. Klootwijk[2], N.A.M. Verhaegh[1], H.H.A.J. Roosen[2], and R.A.M. Wolters[1]
[1]*NXP Semiconductors,* [2]*Philips Research, The Netherlands*

9.3 – Test structure for characterizing metal thickness in damascene CMP technology 210
Alain Toffoli, Sylvain Maitrejean, Jean Duport de Pontcharra, Francois de Crecy, David Bouchu, Lucile Arnaud, Fabien Boulanger
CEA-LETI, Grenoble Cedex, France

9.4 – Test Structure Definition for Dummy Metal Filling Strategy Dedicated to Advanced Integrated RF Inductors 214
Carine Pastore[1,2], Frédéric Gianesello[1], Daniel Gloria[1], Emmanuelle Serret[1], Phillippe Benech[2]
[1]*STMicroelectronics, Crolles,* [2]*IMEP, Grenoble Cedex, France*

SESSION 10: Matching II – Mechanisms

10.1 – Fully considered layout variation analysis and compact modeling of MOSFETs and its application to circuit simulation **223**

Takuji Tanaka[1], Akira Satoh[2], Mitsuru Yamaji[1], Osamu Yamasaki[1], Hiroshi Suzuki[2], Tsuyoshi Sakata[1], Yoshio Inoue[3], Masaru Ito[1], Seiichiro Yamaguchi[1] and Hiroshi Arimoto[1]

[1]*FUJITSU Ltd.,* [2]*FUJITSU Laboratories Ltd.,* [3]*FUJITSU VSLI Ltd. Tokyo, Japan,*

10.2 – On-Mask Mismatch Resistor Structures for the Characterisation of Maskmaking Capability **228**

S. Smith[1], A. Tsiamis[1], M. McCallum[2], A.C. Hourd[3], J.T.M. Stevenson[1], A.J. Walton[1] and S. Enderling[1]

[1]*The University of Edinburgh,* [2]*Nikon Precision Europe GmbH,* [3]*Compugraphics International Ltd., UK*

10.3 – Physics and Modeling of Transistor Matching Degradation under Matched External Stress **233**

Xiaoju Wu, Zhenwu Chen, Praful Madhani

Analog Technology Development, Texas Instruments, TX, USA

10.4 – Influence of STI stress on drain current matching in advanced CMOS . . . 238

Nicole Wils[1], Hans Tuinhout[1], Maurice Meijer[2] [1]*NXP-TSMC Research Center,* [2]*NXP Semiconductor Research, The Netherlands*